

	Hits	Search Text	DBs
6	26	((resist or photoresist or photosensitive or (radiation near5 sensitive)) same pattern\$4 same (etch\$4 or (dry near5 etch\$4) or RIE) same (ARC or antireflect\$4 or BARC or TARC) same (film or coat\$4 or deposit\$4 or layer) same organic) and ((resist or photoresist or photosensitive) same pattern\$4 same (etch\$4 or RIE) same (gas\$4 or (inert\$4 near5 gas\$3) or plasma or ion\$3beam or ion\$4) same (expos\$4 or irradiat\$4 or illuminat\$4)) and ((gate near16 electrode) same (form\$4 or format\$4 or mak\$3 or etch\$5)) and ((implant\$6 or dop\$5) same source same drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
7	164	((resist or photoresist or photosensitive or (radiation near5 sensitive)) same pattern\$4 same (etch\$4 or (dry near5 etch\$4) or RIE) same (ARC or antireflect\$4 or BARC or TARC) same (film or coat\$4 or deposit\$4 or layer) same organic) and ((resist or photoresist or photosensitive) same pattern\$4 same (etch\$4 or RIE) same (gas\$4 or (inert\$4 near5 gas\$3) or plasma or ion\$3beam or ion\$4) same (expos\$4 or irradiat\$4 or illuminat\$4)) and (etch\$4 same (reduc\$4 or decreas\$5) same (size or hole or pattern\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB